

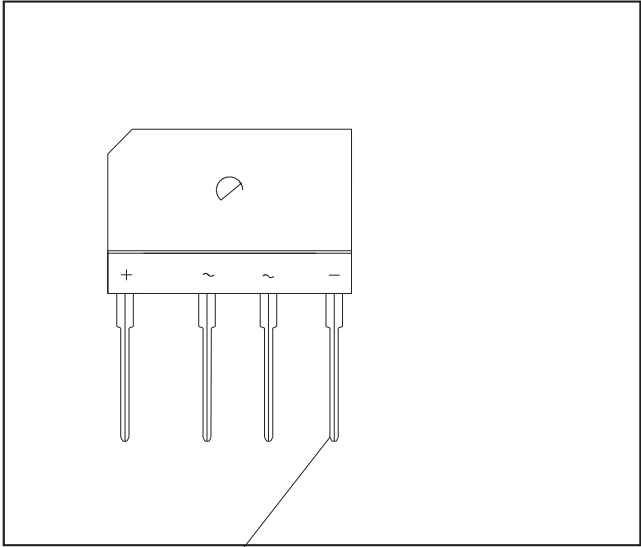
KBJ SILICON BRIDGE RECTIFIER

REVERSE VOLTAGE: 50V --- 1000V CURRENT: 2.0A

FEATURES

MECHANICAL DATA

Mounting position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

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| | | KBJ 2A | KBJ 2B | KBJ 2D | KBJ 2G | KBJ 2J | KBJ 2K | KBJ 2M | UNITS |
|---|-------------|-----------------|--------|--------|--------|--------|--------|--------|----------------------|
| Maximum recurrent peak reverse voltage | V_{RRM} | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum RMS voltage | V_{RMS} | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Maximum DC blocking voltage | V_{DC} | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum average forward Output current @ $T_A=50\text{ }^{\circ}\text{C}$ | $I_{F(AV)}$ | 2.0 | | | | | | | A |
| Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load | I_{FSM} | 50.0 | | | | | | | A |
| Maximum instantaneous forward voltage at 1.0 A | V_F | 1.0 | | | | | | | V |
| Maximum reverse current @ $T_A=25\text{ }^{\circ}\text{C}$ at rated DC blocking voltage @ $T_A=100\text{ }^{\circ}\text{C}$ | I_R | 10.0 1.0 | | | | | | | A mA |
| Typical junction capacitance per element | C_J | 45 | | | | | | | pF |
| Typical thermal resistance | R_{JC} | 2.2 | | | | | | | $^{\circ}\text{C/W}$ |
| Operating junction temperature range | T_J | - 55 ---- + 125 | | | | | | | $^{\circ}\text{C}$ |
| Storage temperature range | T_{STG} | - 55 ---- + 150 | | | | | | | $^{\circ}\text{C}$ |

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC
 2. Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

100

10

1.0

0.1

.01

.2

.4

.6

.8

1.0

1.2

1.4